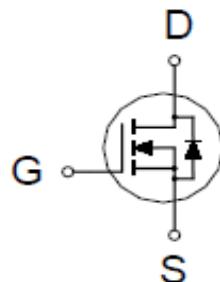
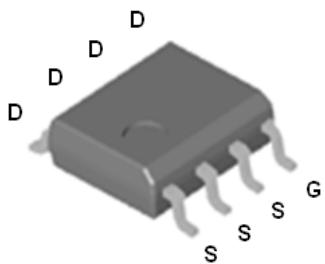


P0903BVA

N-Channel Logic Level Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	9mΩ @ $V_{GS} = 10V$	13A



SOP-8

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A = 25^\circ C$	I_D	13	A
	$T_A = 70^\circ C$		10	
Pulsed Drain Current ¹		I_{DM}	80	
Avalanche Current		I_{AS}	30	
Avalanche Energy	$L = 0.1mH$	E_{AS}	45	mJ
Power Dissipation	$T_A = 25^\circ C$	P_D	2.3	W
	$T_A = 70^\circ C$		1.5	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		55	°C / W
Junction-to-Case	$R_{\theta JC}$		3.7	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$. The value in any given application depends on the user's specific board design

P0903BVA N-Channel Logic Level Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Unless Otherwise Noted)

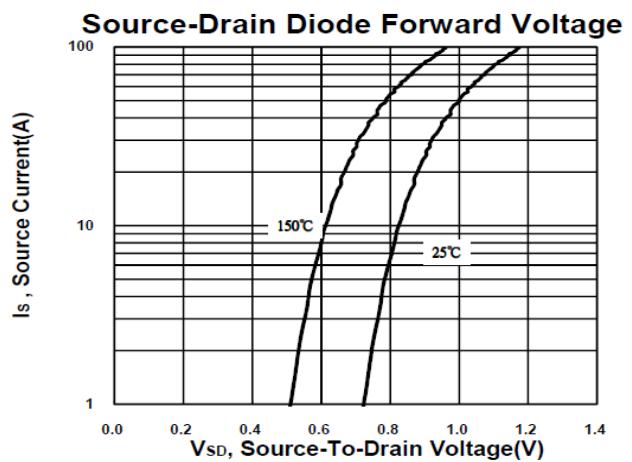
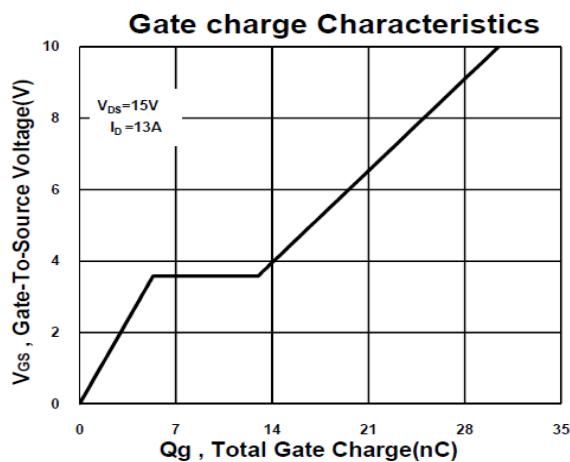
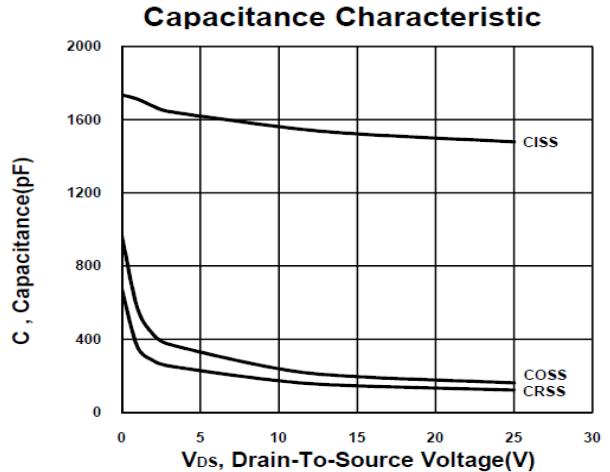
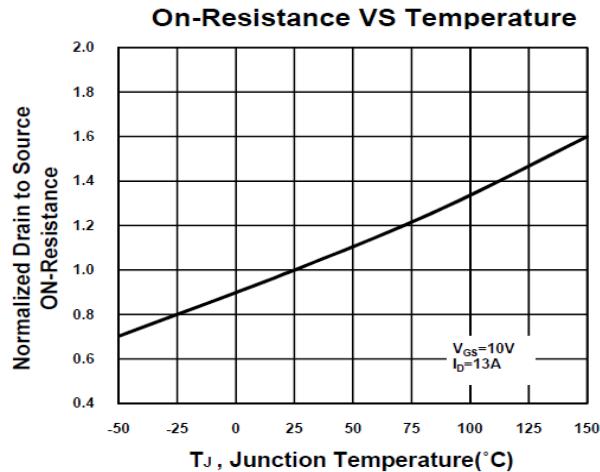
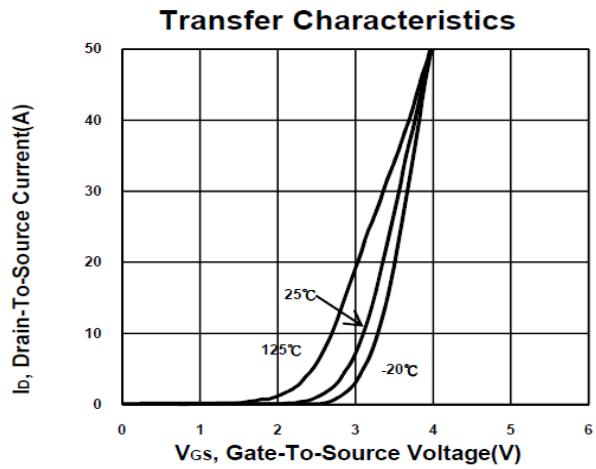
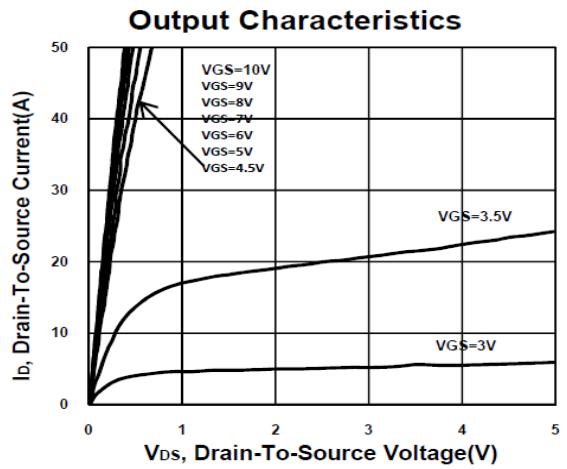
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1	1.7	3	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 24\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
		$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}, T_C = 125^\circ\text{C}$			10	
On-State Drain Current ¹	$I_{\text{D}(\text{ON})}$	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 10\text{V}$	80			A
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 13\text{A}$		11.2	13	$\text{m}\Omega$
		$V_{\text{GS}} = 10\text{V}, I_D = 13\text{A}$		7	9	
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_D = 13\text{A}$		47		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 15\text{V}, f = 1\text{MHz}$		1570		pF
Output Capacitance	C_{oss}			202		
Reverse Transfer Capacitance	C_{rss}			158		
Gate Resistance	R_g	$V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		1.4		Ω
Total Gate Charge ²	$Q_g(V_{\text{GS}}=10\text{V})$	$V_{\text{DS}} = 0.5V_{(\text{BR})\text{DSS}}, I_D = 13\text{A}$		31		nC
	$Q_g(V_{\text{GS}}=4.5\text{V})$			16		
Gate-Source Charge ²	Q_{gs}			5.5		
Gate-Drain Charge ²	Q_{gd}			8		
Turn-On Delay Time ²	$t_{\text{d}(\text{on})}$	$V_{\text{DS}} = 15\text{V}, R_L = 1.5\Omega, I_D \cong 13\text{A}, V_{\text{GS}} = 10\text{V}, R_{\text{GEN}} = 6\Omega$		10.8		nS
Rise Time ²	t_r			16.8		
Turn-Off Delay Time ²	$t_{\text{d}(\text{off})}$			38.4		
Fall Time ²	t_f			19.2		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_A = 25^\circ\text{C}$)						
Continuous Current	I_S				13	A
Forward Voltage ¹	V_{SD}	$I_F = 13\text{A}, V_{\text{GS}} = 0\text{V}$			1.3	V
Diode Reverse Recovery Time	t_{rr}	$I_F = 13\text{A}, dI/dt = 100\text{A} / \mu\text{s}$		15		nS
Diode Reverse Recovery Charge	Q_{rr}			4		nC

¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

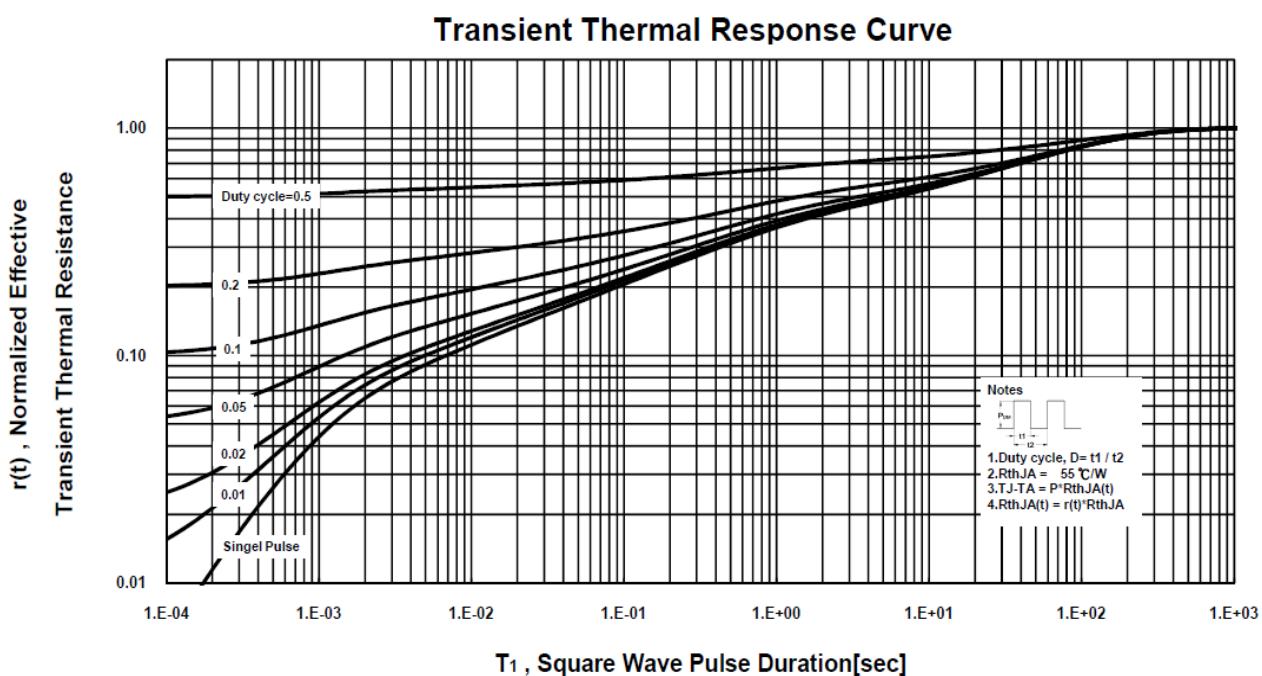
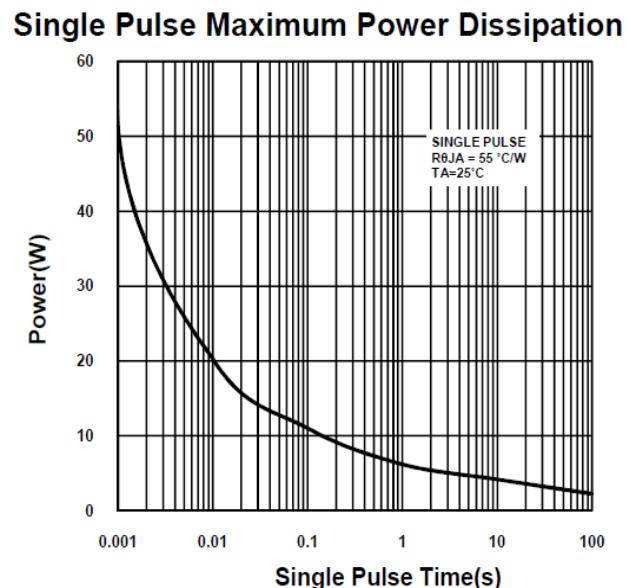
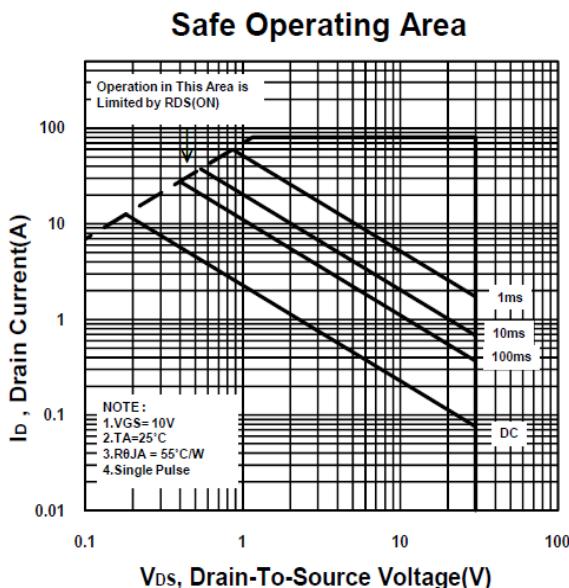
P0903BVA

N-Channel Logic Level Enhancement Mode MOSFET



P0903BVA

N-Channel Logic Level Enhancement Mode MOSFET



P0903BVA

N-Channel Logic Level Enhancement Mode MOSFET

Package Dimension

SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				

